

## **HIGH COUPLING FLOATING GATE TRANSISTOR**

### **ABSTRACT OF THE DISCLOSURE**

The present invention provides methods of fabricating floating gate transistors. One method includes forming laterally spaced source and drain regions to define a channel therebetween, forming a first floating gate portion above the channel region, the first floating gate portion extending in a general horizontal direction, forming spacers over the first floating gate portion to define an exposed region on the first floating gate portion, forming a contact coupled to the first floating gate portion at the exposed region, the contact extending vertically above the first portion, forming a second floating gate portion coupled to the contact, the second floating gate portion extending in a general vertical direction, and forming a control gate adjacent to the second portion.